## P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ m(Ω)	I_D (A)
-20	44 @ V_{GS} = -4.5V	-8.3
	68 @ V_{GS} = -2.5V	-6.7
	150 @ V_{GS} = -1.8V	-4.5

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology
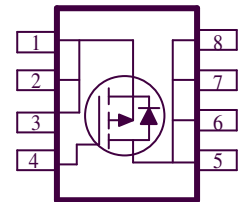
ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	±12	
Continuous Drain Current[a]	T_A=25°C	I_D	-8.3	A
	T_A=70°C		-6.7	
Pulsed Drain Current[b]		I_{DM}	±50	
Continuous Source Current (Diode Conduction)[a]		I_S	-2.1	A
Power Dissipation[a]	T_A=25°C	P_D	3.1	W
	T_A=70°C		2.0	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient[a]	t <= 10 sec	$R_{\theta JA}$	40	°C/W
	Steady-State		70	°C/W

Notes

a.   Surface Mounted on 1" x 1" FR4 Board.

b.   Pulse width limited by maximum junction temperature

SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = -250 uA	-0.7			
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±12 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -16 V, V_{GS} = 0 V			-1	uA
		V_{DS} = -16 V, V_{GS} = 0 V, T_J = 55°C			-5	
On-State Drain Current[A]	$I_{D(on)}$	V_{DS} = -4.5 V, V_{GS} = -10 V	-50			A
Drain-Source On-Resistance[A]	$r_{DS(on)}$	V_{GS} = -4.5 V, I_D = -8.3 A			44	mΩ
		V_{GS} = -2.5 V, I_D = -6.7 A			68	
		V_{GS} = -1.8 V, I_D = -4.5 A			150	
Forward Tranconductance[A]	g_{fs}	V_{DS} = -15 V, I_D = -8.3 A		70		S
Diode Forward Voltage	V_{SD}	I_S = 2.5 A, V_{GS} = 0 V		-0.6		V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = -10 V, V_{GS} = -4.5 V, I_D = -8.3 A		16.7		nC
Gate-Source Charge	Q_{gs}			1.8		
Gate-Drain Charge	Q_{gd}			1.9		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -10 V, R_L = 6 Ω , ID = -1 A, VGEN = -4.5 V		20		nS
Rise Time	t_r			23		
Turn-Off Delay Time	$t_{d(off)}$			289		
Fall-Time	t_f			134		

Notes

a.   Pulse test: PW <= 300us duty cycle <= 2%.

b.   Guaranteed by design, not subject to production testing.
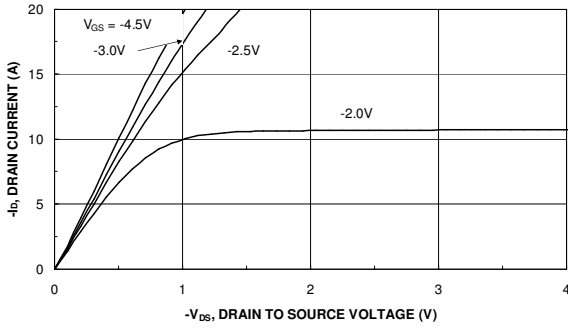
Typical Electrical Characteristics
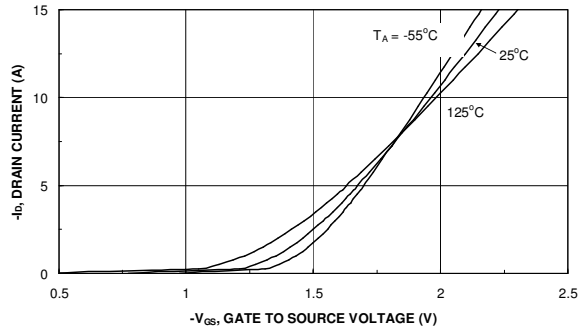
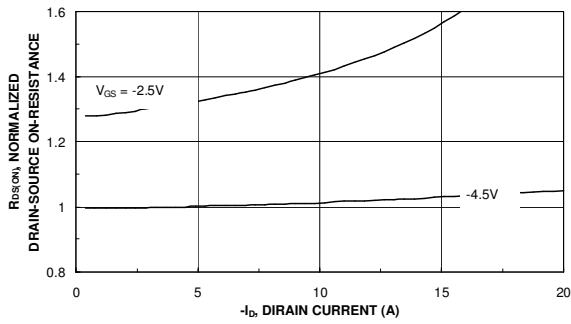**Figure 1. Output Characteristics**

Figure 2. Transfer Characteristics

Figure 3. On-Resistance vs. Drain Current
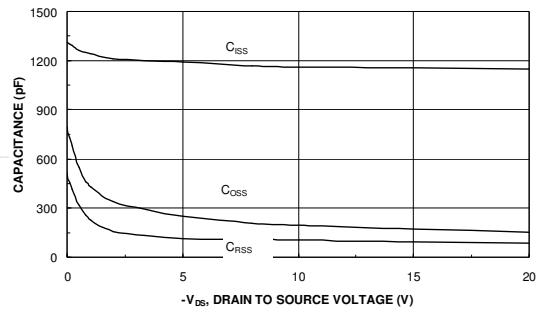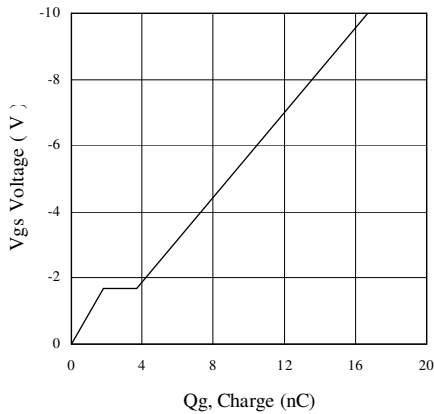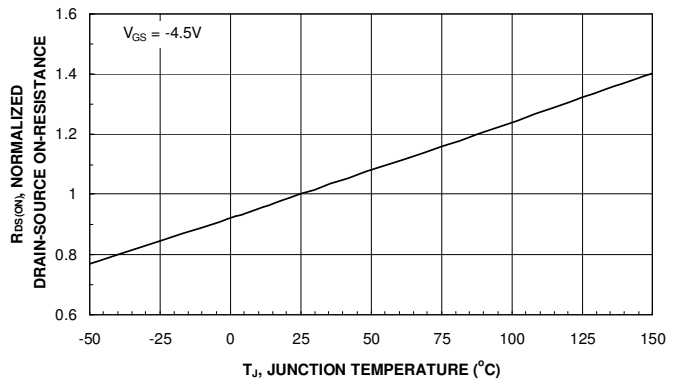
Figure 4. Capacitance

Figure 5. Gate Charge

Figure 6. On-Resistance vs. Junction Temperature

PRELIMINARY

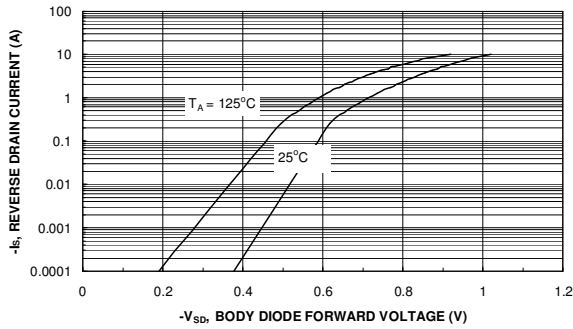# Typical Electrical Characteristics

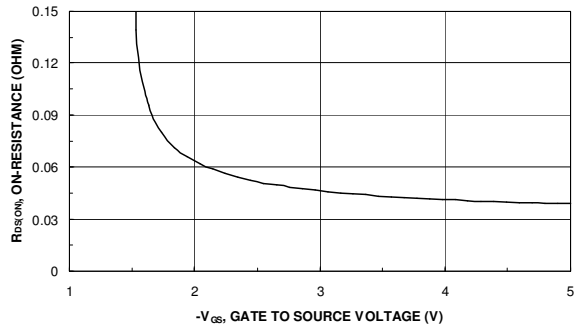**Figure 7. Source-Drain Diode Forward Voltage**

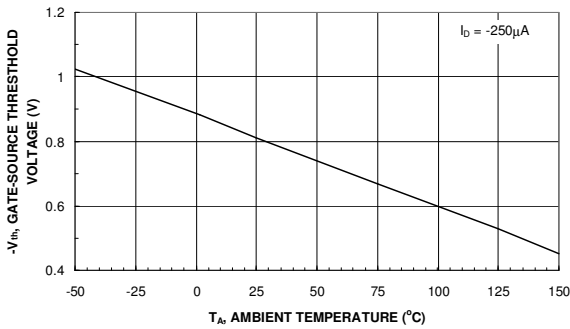**Figure 8. On-Resistance with Gate to Source Voltage**

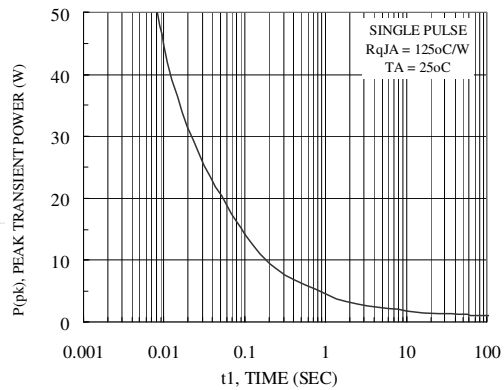**Figure 9. Vth Gate to Source Voltage Vs Temperature**

Figure 10. Single Pulse Maximum Power Dissipation
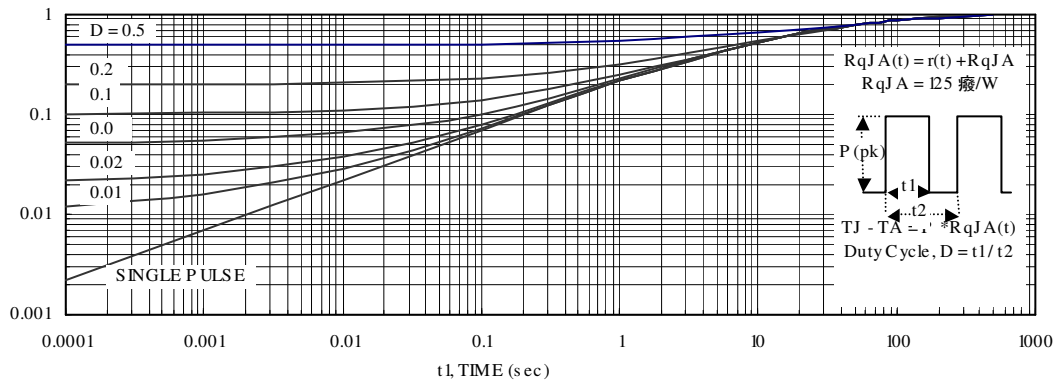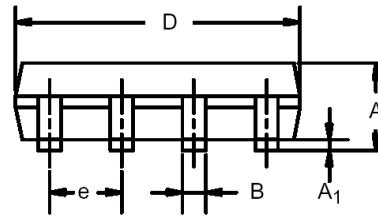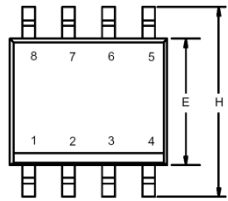
Normalized Thermal Transient Junction to Ambient

Figure 11. Transient Thermal Response Curve

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Package Information

SO-8: 8LEAD

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A_1	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°

PRELIMINARY